



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD OF FORMING A POLYSILICON RESISTOR		
Application Type : regular, utility Attorney Docket Number : NAUP0525USA			
Correspondence address: Customer Number: 027765			
			
Inventor Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Cheng-Hsiung Family Name: Chen Residence: City of Residence: Taipei City Country of Residence: TW Address-1 of Mailing Address: 13F, No. 70, Lane 134, Sec. 3, Hsin-Yi Rd. Address-2 of Mailing Address: City of Mailing Address: Taipei City State of Mailing Address: Postal Code of Mailing Address: Country of Mailing Address: TW Phone: Fax: E-mail:			
Attorney Information: practitioner(s) at Customer Number: 027765			
 as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			